

Ateeq J Suria

List of Publications by Year in descending order

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Version: 2024-02-01

12

papers

165

citations

1478505

6

h-index

1588992

8

g-index

12

all docs

12

docs citations

12

times ranked

278

citing authors

#	ARTICLE	IF	CITATIONS
1	Suppression of Persistent Photoconductivity in AlGaN/GaN Ultraviolet Photodetectors Using <italic>In Situ</italic> Heating. IEEE Electron Device Letters, 2017, 38, 56-59.	3.9	68
2	DC characteristics of ALD-grown Al ₂ O ₃ /AlGaN/GaN MIS-HEMTs and HEMTs at 600 Å°C in air. Semiconductor Science and Technology, 2016, 31, 115017.	2.0	22
3	Tuning Electrical and Thermal Transport in AlGaN/GaN Heterostructures via Buffer Layer Engineering. Advanced Functional Materials, 2018, 28, 1705823.	14.9	19
4	A microfabricated sun sensor using GaN-on-sapphire ultraviolet photodetector arrays. Review of Scientific Instruments, 2016, 87, 095003.	1.3	16
5	Thickness engineering of atomic layer deposited Al ₂ O ₃ films to suppress interfacial reaction and diffusion of Ni/Au gate metal in AlGaN/GaN HEMTs up to 600 Å°C in air. Applied Physics Letters, 2017, 110, .	3.3	12
6	Multilayer etch masks for 3-dimensional fabrication of robust silicon carbide microstructures. , 2015, , .		9
7	Degradation of 2DEG transport properties in GaN-capped AlGaN/GaN heterostructures at 600 Å°C in oxidizing and inert environments. Journal of Applied Physics, 2017, 122, .	2.5	9
8	Effects of radiation and temperature on gallium nitride (GaN) metal-semiconductor-metal ultraviolet photodetectors. , 2014, , .		5
9	Thermoelectrics: Tuning Electrical and Thermal Transport in AlGaN/GaN Heterostructures via Buffer Layer Engineering (Adv. Funct. Mater. 22/2018). Advanced Functional Materials, 2018, 28, 1870152.	14.9	3
10	Irradiation Response of Graphene Enhanced Gallium Nitride Metal-Semiconductor-Metal Ultraviolet Photodetectors. Materials Research Society Symposia Proceedings, 2015, 1746, 13.	0.1	1
11	Car Storytelling and Interaction Design. , 0, , .		1
12	Gallium Nitride Microelectronics for High-Temperature Environments. , 2016, , 395-433.		0